ZXMP4A16K 40V P-channel enhancement mode MOSFET

Summary

 $V_{(BR)DSS}$ = -40V; $R_{DS(ON)}$ = 0.060 Ω I_D= -9.9A

Description

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- DPAK package

Applications

- DC DC converters
- Audio output stages
- Relay and solenoid driving
- Motor control

Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXMP4A16KTC	13	16mm	2500 units

Device marking

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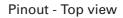
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ZXMP 4A16

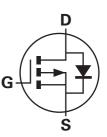




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Absolute maximum rating

Parameter	Symbol	Limit	Unit
Drain-source voltage	V _{DSS}	-40	V
Gate-source voltage	V _{GS}	±20	V
Continuous drain current			
V _{GS} = -10V; T _A =25°C ^(b)		-9.9	А
V _{GS} = -10V; T _A =70°C ^(b)	۱ _D	-8.0	А
V_{GS} = -10V; T_A =25°C ^(a)		-6.6	А
Pulsed drain current ^(c)	I _{DM}	-35	А
Continuous source current (body diode) ^(b)	۱ _S	-10.1	А
Pulsed source current (body diode) ^(c)	I _{SM}	-35	А
Power dissipation at T _A =25°C ^(a)	PD	4.2	W
Linear derating factor		33.6	mW/°C
Power dissipation at $T_A=25^{\circ}C^{(b)}$	PD	9.5	W
Linear derating factor		76	mW/°C
Power dissipation at T _A =25°C ^(d) Linear derating factor	P _D	2.15 17.2	W mW/°C
Operating and storage temperature range	T _j :T _{stg}	-55 to +150	°C
Thermal resistance		•	
Parameter	Symbol	Value	Unit
Junction to ambient ^(a)	R _{⊖JA}	30	°C/W
Junction to ambient ^(b)	R _{OJA}	13.2	°C/W
Junction to ambient ^(d)	R _{OJA}	58	°C/W

NOTES:

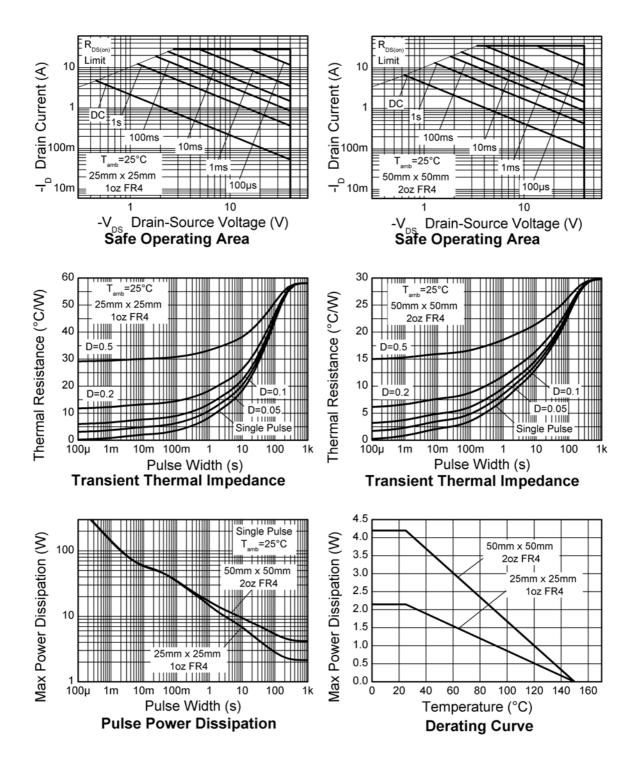
(a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at t \leq 10 sec.

(c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D=0.02 pulse width=300µs - pulse width limited by maximum junction temperature.

(d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Characteristics



Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Static							
Drain-source breakdown voltage	V _{(BR)DSS}	-40			V	I _D =-250μA, V _{GS} =0V	
Zero gate voltage drain current	I _{DSS}			-1	μA	V_{DS} =-40V, V_{GS} =0V	
Gate-body leakage	I _{GSS}			100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-source threshold voltage	V _{GS(th)}	-1.0			V	I _D =-250μA, V _{DS} =V _{GS}	
Static drain-source on-state	R _{DS(on)}			0.060	Ω	V _{GS} =-10V, I _D =-3.8A	
resistance ^(*)				0.100	Ω	V _{GS} =-4.5V, I _D =-2.9A	
Forward transconductance (*)(‡)	9 _{fs}		7.4		S	V _{DS} =-15V,I _D =-3.8A	
Dynamic ^(‡)				•			
Input capacitance	C _{iss}		965		pF	V _{DS} =-20V, V _{GS} =0V, f=1MHz	
Output capacitance	C _{oss}		180		pF		
Reverse transfer capacitance	C _{rss}		158		pF		
Switching ^{(†) (‡)}							
Turn-on delay time	t _{d(on)}		4.0		ns		
Rise time	t _r		6.0		ns	V _{DD} =-20V, I _D =-1A	
Turn-off delay time	t _{d(off)}		36.8		ns	R _G =6.0Ω,V _{GS} =-10V	
Fall time	t _f		17.1		ns		
Gate charge	Qg		16.5		nC	V _{DS} =-20V,V _{GS} =-5V, I _D =-3.8A	
Total gate charge	Qg		29.6		nC		
Gate-source charge	0 _{gs}		2.8		nC		
Gate-drain charge	0 _{gd}		8.1		nC		
Source-drain diode				•	•		
Diode forward voltage ^(*)	V _{SD}		-0.89	-1.2	V	T _J =25°C, I _S =-3.8A, V _{GS} =0V	
Reverse recovery time ^(‡)	t _{rr}		29.8		ns	T _J =25°C, I _F =-3.8A,	
Reverse recovery charge ^(‡)	Q _{rr}		37.2		nC	di/dt= 100A/μs	

Electrical characteristics (at $T_A = 25^{\circ}C$ unless otherwise stated)

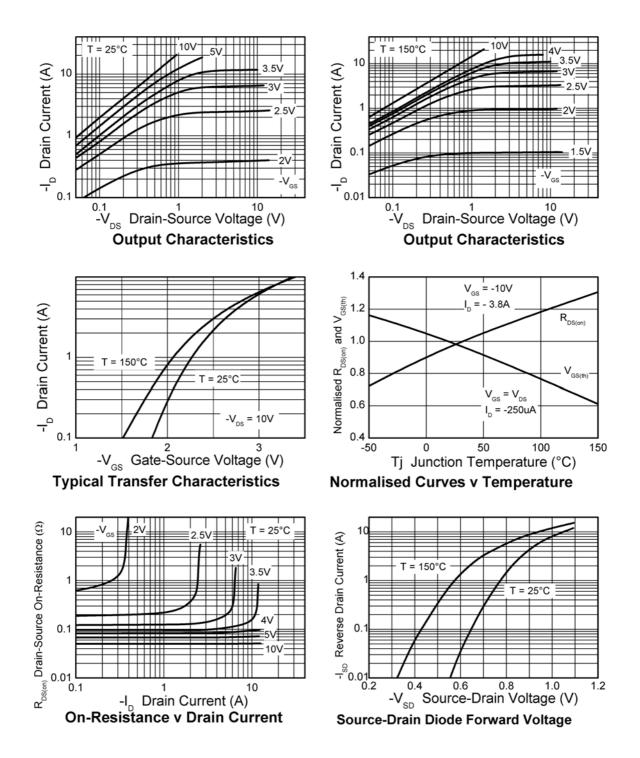
NOTES:

(*) Measured under pulsed conditions. Width \leq 300µs. Duty cycle \leq 2%.

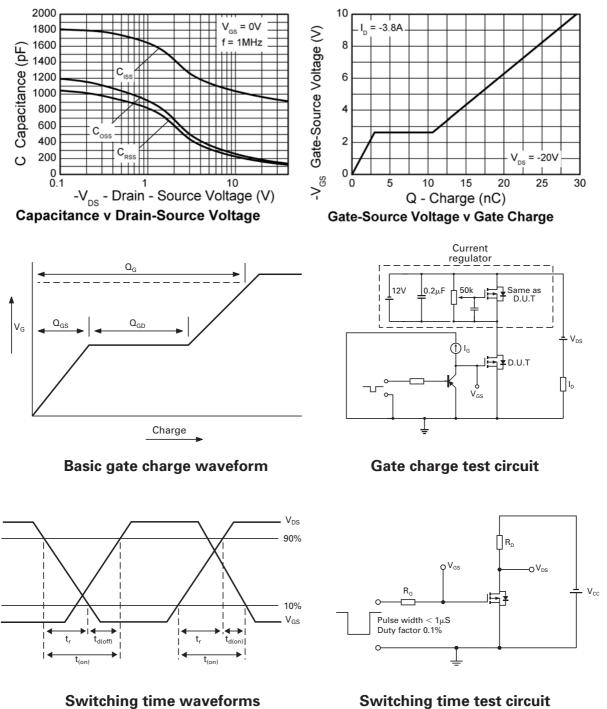
(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

Typical characteristics



Typical characteristics

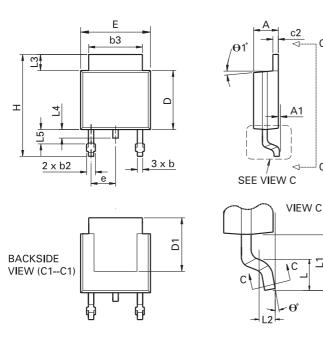


Switching time test circuit

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Package details - DPAK



Package dimensions

Dim.	Inc	hes	Millin	neters	Dim.	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

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Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

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